

1.0 SCOPE

This specification documents the detail requirements for space qualified die per MIL-PRF-38534 class K except as modified herein.

The manufacturing flow described in the SPACE DIE BROCHURE is to be considered a part of this specification.

This datasheet specifically details the space grade version of this product. A more detailed operational description and a complete datasheet for commercial product grades can be found at <https://www.analog.com/hmc939>

2.0 Part Number: The complete part number(s) of this specification follows:

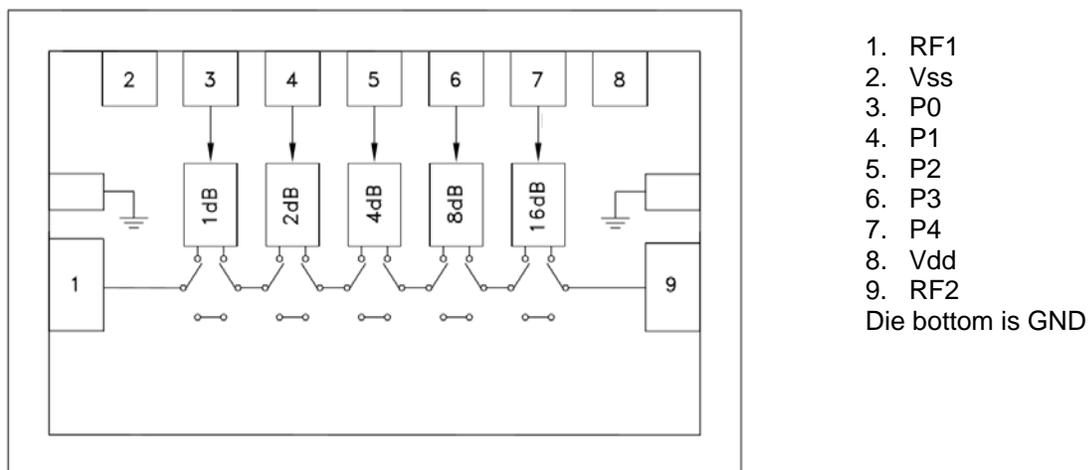
<u>Specific Part Number</u>	<u>Description</u>
ADH939-000C	0.1 GHz to 40 GHz, GaAs, MMIC, 5-Bit 1.0 dB LSB, Digital Attenuator Die

3.0 Die Information

3.1. Die Dimensions

Die Size	Die Thickness	Bond Pad and Backside Metallization
90.2 mils x 37.4 mils	4 mils	Au

3.2. Die Picture



ASD0016599

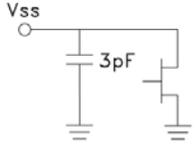
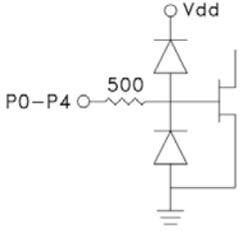
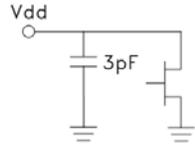
Rev. B

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3.3. Pad Descriptions

Pad Number	Function	Description	Interface Schematic
Die Bottom	GND	Die bottom must be connected to RF ground.	
1, 9	RF1, RF2	This pad is DC coupled and matched to 50 Ohm. Blocking capacitors are required if RF line potential is not equal to 0 V.	
2	Vss	Negative Bias -5 V.	
3 - 7	P0 - P4	See Truth Table (Table IV) and Control Voltage Table (Table V).	
8	Vdd	Positive Bias +5 V.	

4.0 Specifications

4.1. Absolute Maximum Ratings 1/

RF Input Power (0.1 GHz to 40 GHz)	+25 dBm
Control Voltage (P0 to P4)	Vdd + 0.5 V
Vdd	+7 V dc
Vss	-7 V dc
Channel Temperature	150 °C
Thermal Resistance (Junction to die bottom)	144 °C/W
Storage Temperature Range	-65 °C to +150 °C
Operating Temperature Range	-55 °C to +85 °C
ESD Sensitivity (HBM)	Class 1A passed 250 V

4.2. Nominal Operating Performance Characteristics 2/

Insertion Loss (40 GHz)	6.4 dB
Attenuation Accuracy: 1-15 dB States (40 GHz) 3/	± (0.5 + 5 % of Atten. Setting) Max dB
Attenuation Accuracy: 16-31 dB States (40 GHz) 3/	± (0.6 + 6 % of Atten. Setting) Max dB
Return Loss RF1 & RF2 (40 GHz) 4/	13 dB

1/ Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions outside of those indicated in the operation sections of this specification is not implied. Exposure to absolute maximum ratings for extended periods may affect device reliability.

2/ All specifications apply with T_A = 25 °C, V_{dd} = 5 V, V_{ss} = -5 V and P0-P4 = 0/+5 V unless otherwise noted.

3/ Referenced to insertion loss.

4/ Applies across all attenuator states.

5.0 Die Qualification

In accordance with class-K version of MIL-PRF-38534, Appendix C, Table C-II, except as modified herein.

- (a) Pre-screen test post assembly required prior to die qualification, to remove all assembly related rejects.
- (b) Mechanical Shock or Constant Acceleration not performed.
- (c) Interim and post burn-in electrical tests will include static tests screened at +25 °C only.

6.0 Dice Electrical Characteristics

TABLE I – DIE ELECTRICAL CHARACTERISTICS					
Parameter	Symbol	Conditions 1/2/3/4/ Unless otherwise specified	Limits		Unit
			Min	Max	
Insertion Loss	IL	2 GHz & 8 GHz		5	dB
		26 GHz		7.5	
Attenuation Accuracy 1-15 dB States 5/ 6/	AA		± (0.5 + 5 % of Atten. Setting) Max		dB
Attenuation Accuracy 16-31 dB States 5/ 6/	AA		± (0.6 + 6 % of Atten. Setting) Max		dB
V _{dd} Supply Current	I _{dd}		2	6	mA
V _{ss} Supply Current	I _{ss}		-7	-3	mA

TABLE I Notes:

1/ Limits apply at T_A = +25 °C only.

2/ RF1 = 10 dBm, V_{dd} = 5 V and V_{ss} = -5 V.

3/ P0 – P4 Low = 0.8 V, High = 2.0 V.

4/ Parameters measured at 2 GHz, 8 GHz & 26 GHz unless otherwise specified.

5/ Measured at major attenuation states only as shown in Table IV.

6/ Referenced to insertion loss.

TABLE II – ELECTRICAL CHARACTERISTICS FOR QUALIFICATION SAMPLES

Parameter	Symbol	Conditions <u>1/2/3/4/</u> Unless otherwise specified	Sub-Group	Limits		Unit
				Min	Max	
Insertion Loss	IL	2 GHz & 8 GHz	4		5	dB
			5, 6		6	
		26 GHz	4		7.5	
			5, 6		8.5	
Attenuation Accuracy: 1-15 dB States <u>5/ 6/</u>	AA		4, 5, 6	± (0.5 + 5 % of Atten. Setting) Max		dB
Attenuation Accuracy: 16-31dB States <u>5/ 6/</u>	AA		4, 5, 6	± (0.6 + 6 % of Atten. Setting) Max		dB
Return Loss RF1 & RF2 <u>5/</u>	S11, S22		4	7		dB
			5,6	5		
Vdd Supply Current	Idd		1	3	7	mA
			2, 3	2	9	
Vss Supply Current	Iss		1	-8	-4	mA
			2, 3	-10	-3	

TABLE II Notes:

1/ T_A Nom = +25 °C, T_A Max = +85 °C, T_A Min = -40 °C.

2/ RF1 = 0 dBm, Vdd = 5 V and Vss = -5 V.

3/ P0 – P4: Low = 0.8 V, High = 2.0 V.

4/ Parameters measured at 2 GHz, 8 GHz & 26 GHz unless otherwise specified.

5/ Measured at major attenuation states only as shown in Table IV.

6/ Referenced to insertion loss.

TABLE III – BURN-IN/LIFE TEST DELTA LIMITS 1/ 2/ 3/ 4/

Parameter	Symbol	Delta	Units
Insertion Loss	IL	± 1	dB
Vdd Supply Current	Idd	± 10	%
Vss Supply Current	Iss	± 10	%

TABLE III Notes:

1/ 240 hour burn-in and 1000 hour life test end point electrical parameters.

2/ Deltas are performed at T_A = +25 °C only.

3/ Product is tested in accordance with conditions in Table II.

4/ Table II limits will not be exceeded.

TABLE IV – TRUTH TABLE 1/					Attenuation State RF1 – RF2
P4 (16 dB)	P3 (8 dB)	P2 (4 dB)	P1 (2 dB)	P0 (1 dB)	
High	High	High	High	High	Reference I.L.
High	High	High	High	Low	1 dB
High	High	High	Low	High	2 dB
High	High	Low	High	High	4 dB
High	Low	High	High	High	8 dB
Low	High	High	High	High	16 dB
Low	Low	Low	Low	Low	31 dB

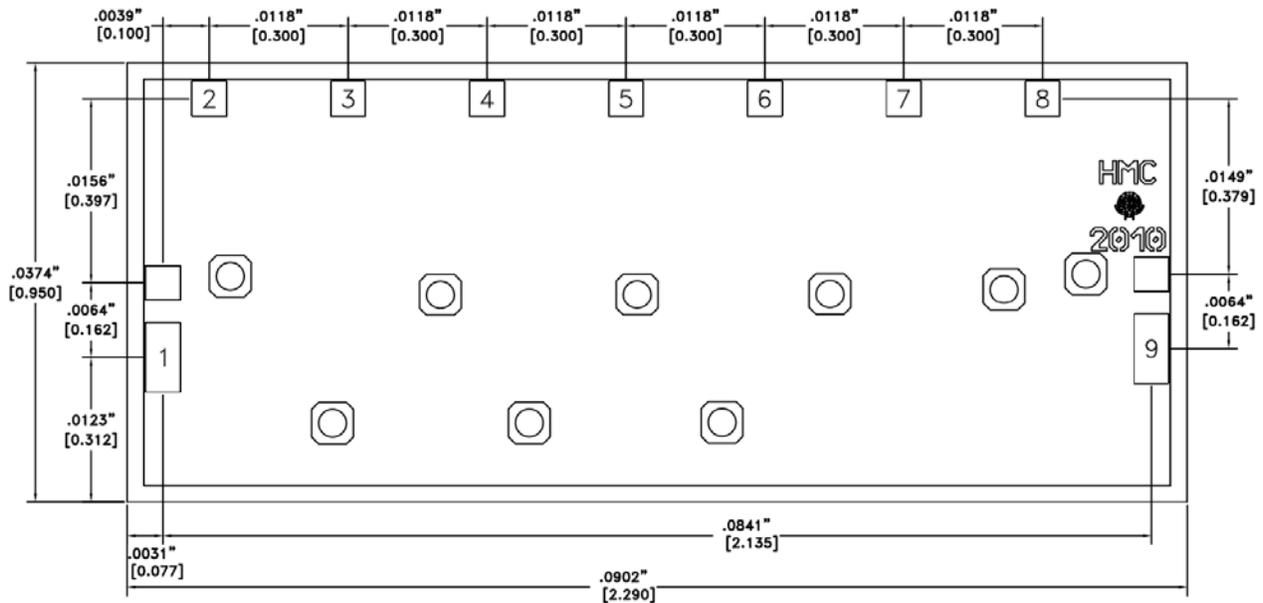
TABLE IV Note:

1/ Any combination of the above states will provide an attenuation approximately equal to the sum of the bits selected.

TABLE V – CONTROL VOLTAGE	
State	Bias Condition
Low	0 V to 0.8 V at 1 μ A
High	2 V to 5 V at 1 μ A

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7.0 Die Outline



PAD	DESCRIPTION	PAD SIZE
1	RF1	.0059[.150] X .0030[.075]
2	Vss	.0030[.075] X .0030[.075]
3	PO	.0030[.075] X .0030[.075]
4	P1	.0030[.075] X .0030[.075]
5	P2	.0030[.075] X .0030[.075]
6	P3	.0030[.075] X .0030[.075]
7	P4	.0030[.075] X .0030[.075]
8	Vdd	.0030[.075] X .0030[.075]
9	RF2	.0059[.150] X .0030[.075]

NOTES:

1. ALL DIMENSIONS ARE IN INCHES [MM]
2. DIE THICKNESS IS .004"
3. TYPICAL BOND PAD IS .003" SQUARE
4. BOND PAD METALIZATION: GOLD
5. BACKSIDE METALIZATION: GOLD
6. BACKSIDE METAL IS GROUND
7. OVERALL DIE SIZE $\pm .002$ "
8. THERE ARE NO AIR BRIDGES ON THIS DIE

8.0 Application Notes

Figure 1 shows the assembly diagram. The die should be attached directly to the ground plane eutectically or with conductive epoxy. 50 Ω microstrip transmission lines on 0.127 mm (5 mil) thick alumina thin film substrates are recommended for bringing RF to and from the chip (Figure 2). If 0.254 mm (10 mil) thick alumina thin film substrates must be used, the die should be raised 0.15 mm (6 mil) so that the surface of the die is coplanar with the surface of the substrate. One way to accomplish this is to attach the 0.102 mm (4 mil) thick die to a 0.150 mm (6 mil) thick molybdenum heat spreader (moly-tab) which is then attached to the ground plane (Figure 3). Microstrip substrates should be brought as close to the die as possible in order to minimize wire bond length. Typical die-to-substrate spacing is 0.076 mm to 0.152 mm (3 to 6 mils).

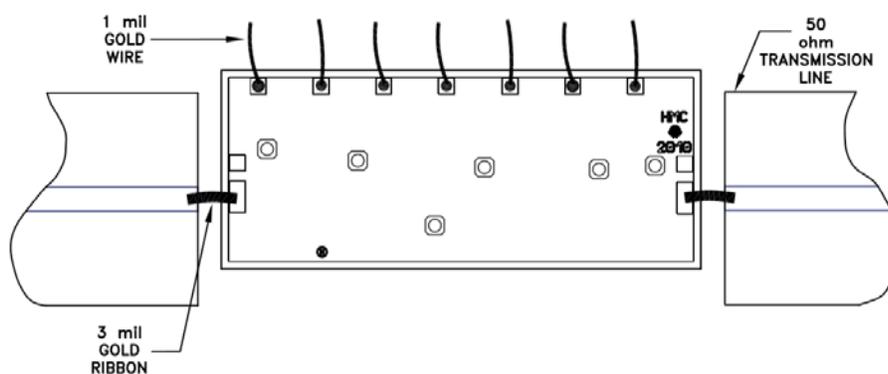


Figure 1. Assembly Diagram

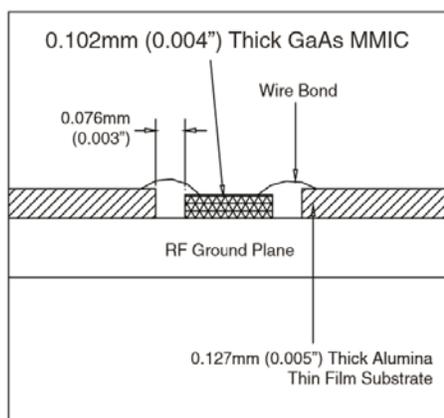


Figure 2. Die without Moly Tab

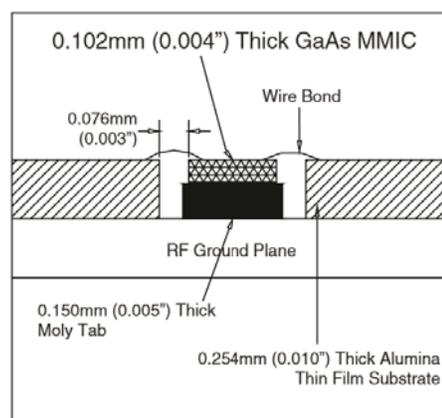


Figure 3. Die with Moly Tab

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Die Packaging Information

Standard	Alternate
GP-2 (Gel Pack)	<u>1/</u>

Note:

1/ For alternate packaging information, contact Analog Devices Inc.

Rev	Description of Change	Date
A	Production release.	28-February-2020
B	Corrected AMR RF Input Frequency Range, corrected AMR Vss polarity	4-October-2021